

**Amendments to the Claims:**

Claims 1-24 (Canceled).

25. (Currently Amended): A process of forming MRAM circuitry, comprising:

forming an MRAM cell comprising magnetic material over a substrate;

chemical vapor depositing a ~~silicon carbide-comprising~~ silicon carbide-comprising layer over the MRAM cell at a temperature of no greater than 500°C;

forming an insulative material over the ~~silicon carbide-comprising~~ silicon carbide-comprising layer;

etching a contact opening through the insulative material using the ~~silicon carbide-comprising~~ silicon carbide-comprising layer as an etch stop; and

plasma etching within the contact opening through the ~~silicon carbide-comprising~~ silicon carbide-comprising layer using a gas chemistry comprising oxygen and hydrogen to extend the contact opening through the ~~silicon carbide-comprising~~ silicon carbide-comprising layer to the magnetic material of the MRAM cell, and under conditions which etch the ~~silicon carbide-comprising~~ silicon carbide-comprising layer at a rate at least twice that of any etching of the insulative material.

26. (Original): The method of claim 25 wherein the MRAM cell comprises a dielectric layer sandwiched between magnetic material layers.

27. (Original): The method of claim 25 wherein the insulative material comprises SiO<sub>2</sub>.

28. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 200°C.

29. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than 500°C between the depositing and the etching.

30. (Original): The method of claim 25 wherein the substrate is not exposed to a temperature greater than the highest temperature during the depositing between the depositing and the etching.

31. (Original): The method of claim 25 comprising conducting the chemical vapor depositing at a temperature of no greater than 250°C, and wherein the substrate is not exposed to a temperature greater than 250°C between the depositing and the etching.

32. (Original): The method of claim 25 wherein the oxygen is derived from the group consisting of O<sub>2</sub>, O<sub>3</sub>, NO<sub>x</sub>, CO, CO<sub>2</sub>, and mixtures thereof.

33. (Original): The method of claim 25 wherein the hydrogen is derived from the group consisting of H<sub>2</sub>, NH<sub>3</sub>, CH<sub>4</sub>, and mixtures thereof.

34. (Original): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed within the chamber.

35. (Original): The method of claim 25 comprising after the plasma etching, forming conductive material within the contact opening.

Claims 36-47 (Canceled).

48. (Previously Presented): The method of claim 25 wherein the chemical vapor depositing is plasma enhanced.

49. (Previously Presented): The method of claim 25 wherein, the oxygen is derived from the group consisting of O<sub>2</sub>, O<sub>3</sub>, NO<sub>x</sub>, CO, CO<sub>2</sub>, and mixtures thereof; and

the hydrogen is derived from the group consisting of H<sub>2</sub>, NH<sub>3</sub>, CH<sub>4</sub>, and mixtures thereof.

50. (Previously Presented): The method of claim 25 wherein the oxygen is derived at least in part from O<sub>2</sub> and the hydrogen is derived at least in part from NH<sub>3</sub>.

51. (Previously Presented): The method of claim 25 wherein the plasma etching is conducted within a chamber, plasma during the plasma etching being first formed remote from the chamber.

52. (Currently Amended): The method of claim 25 comprising plasma etching under conditions which etch the ~~silicon carbide comprising~~ silicon carbide-comprising layer at a rate at least three times that of any etching of the insulative material.

53. (Currently Amended): The method of claim 25 comprising plasma etching under conditions which etch the ~~silicon carbide comprising~~ silicon carbide-comprising layer at a rate at least four times that of any etching of the insulative material.

54. (Previously Presented): The method of claim 25 wherein the oxygen is derived from a gas comprising O<sub>2</sub>.

55. (Previously Presented): The method of claim 25 wherein the oxygen is derived from a gas comprising O<sub>3</sub>.

56. (Previously Presented): The method of claim 25 wherein the oxygen is derived from a gas comprising NO<sub>x</sub>.

57. (Previously Presented): The method of claim 25 wherein the oxygen is derived from a gas comprising CO.

58. (Previously Presented): The method of claim 25 wherein the oxygen is derived from a gas comprising CO<sub>2</sub>.

59. (Previously Presented): The method of claim 25 wherein the hydrogen is derived from a gas comprising H<sub>2</sub>.

60. (Previously Presented): The method of claim 25 wherein the hydrogen is derived from a gas comprising  $\text{NH}_3$ .

61. (Previously Presented): The method of claim 25 wherein the hydrogen is derived from a gas comprising  $\text{CH}_4$ .